

- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary



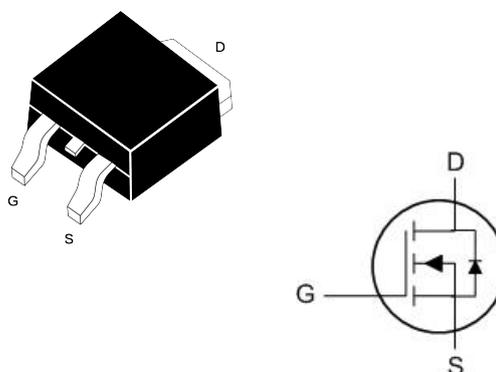
BVDSS	RDSON	ID
100V	32 mΩ	30A

Description

The JH30N10 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The JH30N10 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO-252 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	30	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	15	A
I_{DM}	Pulsed Drain Current ²	80	A
EAS	Single Pulse Avalanche Energy ³	4 0	mJ
I_{AS}	Avalanche Current	30	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ³	43.7	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	50	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	3.0	$^\circ C/W$

Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100	-	-	V	
Gate-body Leakage current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100V, V _{GS} = 0V	T _J = 25°C	-	-	1	μA
			T _J = 100°C	-	-	100	
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.2	-	2.5	V	
Drain-Source on-Resistance ⁴	R _{DS(on)}	V _{GS} = 10V, I _D = 5A	-	32	45	mΩ	
		V _{GS} = 4.5V, I _D = 3A	-	38	75		
Forward Transconductance ⁴	g _{fs}	V _{DS} = 5V, I _D = 5A	-	12	-	S	
Dynamic Characteristics⁵							
Input Capacitance	C _{iss}	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz	-	2420	-	pF	
Output Capacitance	C _{oss}		-	99	-		
Reverse Transfer Capacitance	C _{rss}		-	84	-		
Gate Resistance	R _g	f = 1MHz	-	1.3	-	Ω	
Switching Characteristics⁵							
Total Gate Charge	Q _g	V _{GS} = 10V, V _{DS} = 50V, I _D = 5A	-	40.6	-	nC	
Gate-Source Charge	Q _{gs}		-	8	-		
Gate-Drain Charge	Q _{gd}		-	6.7	-		
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DD} = 50V, R _G = 3Ω, I _D = 5A	-	8.7	-	ns	
Rise Time	t _r		-	41	-		
Turn-Off Delay Time	t _{d(off)}		-	40	-		
Fall Time	t _f		-	32	-		
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴	V _{SD}	I _S = 1A, V _{GS} = 0V	-	-	1.2	V	
Continuous Source Current	I _S	T _C = 25°C	-	-	30	A	

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)} = 150°C.
2. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%
3. The EAS data shows Max. rating. The test condition is V_{DD} = 25V, V_{GS} = 10V, L = 0.1mH, I_{AS} = 8A
4. The power dissipation is limited by 150°C junction temperature
5. The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

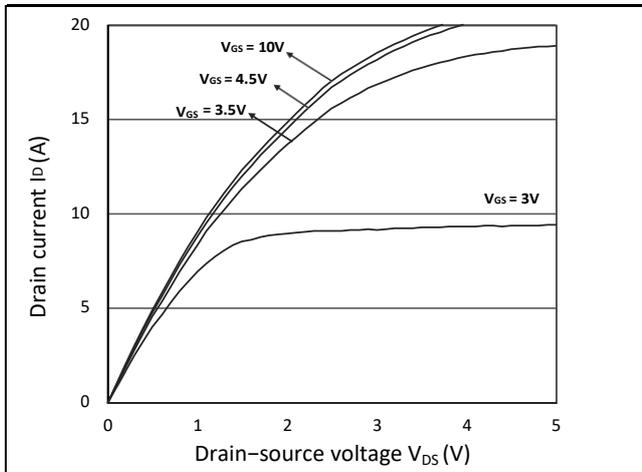


Figure 1. Output Characteristics

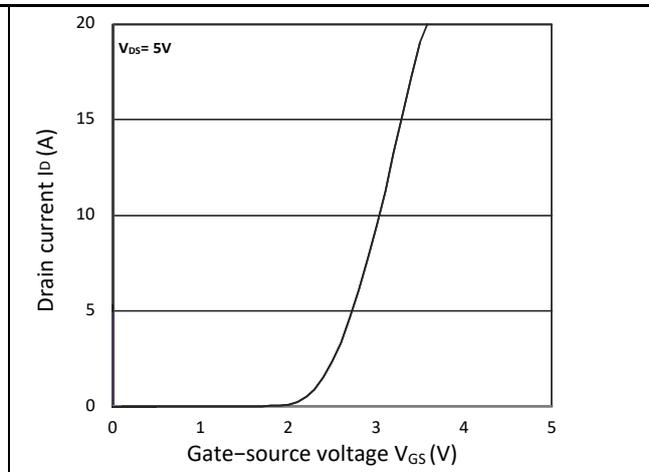


Figure 2. Transfer Characteristics

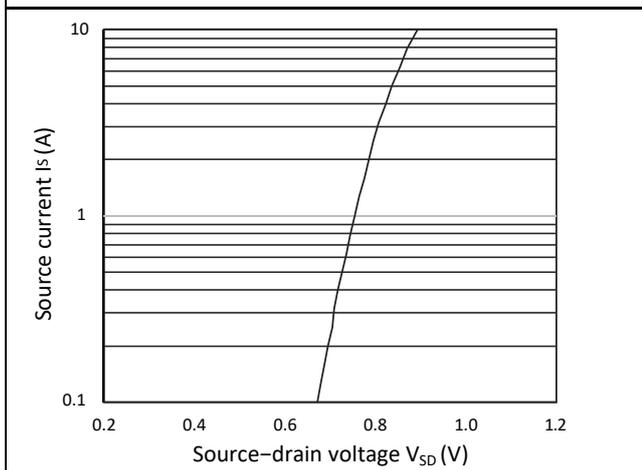


Figure 3. Forward Characteristics of Reverse

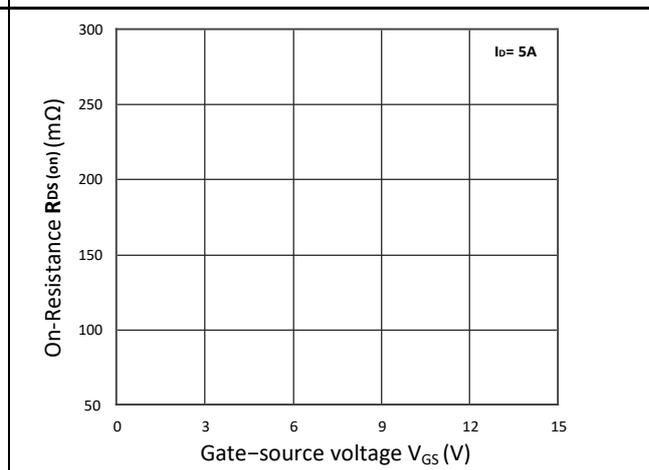


Figure 4. $R_{DS(on)}$ vs. V_{GS}

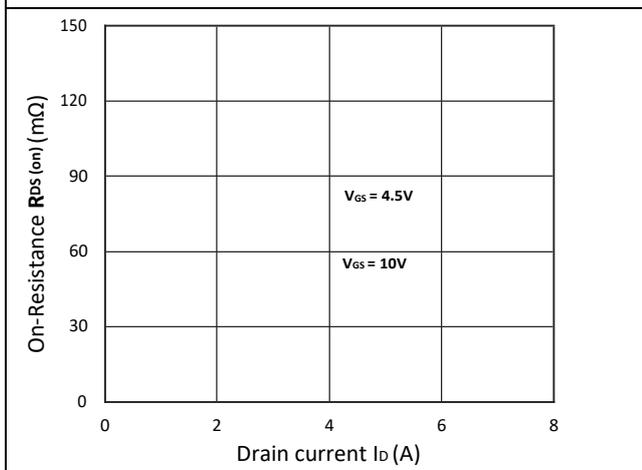


Figure 5. $R_{DS(on)}$ vs. I_D

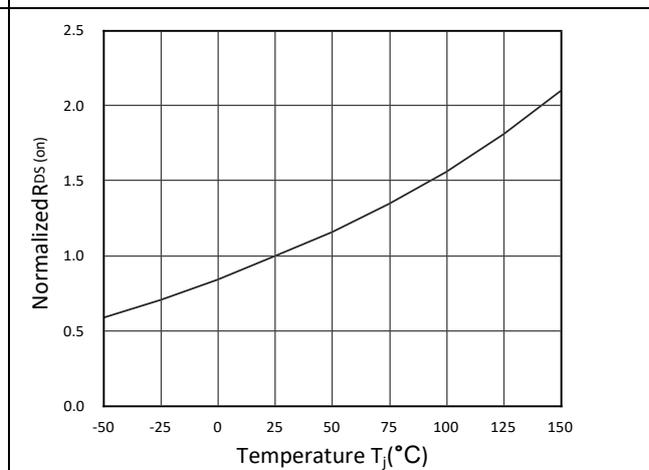


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

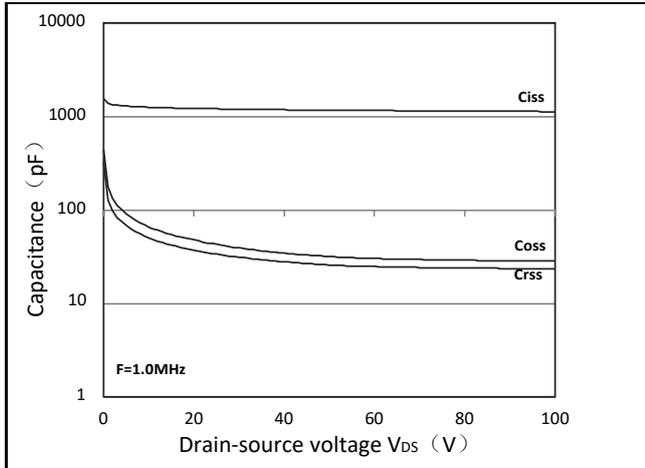


Figure 7. Capacitance Characteristics

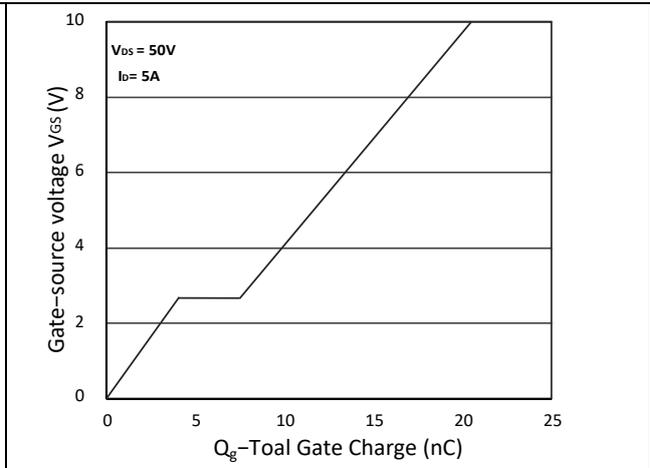


Figure 8. Gate Charge Characteristics

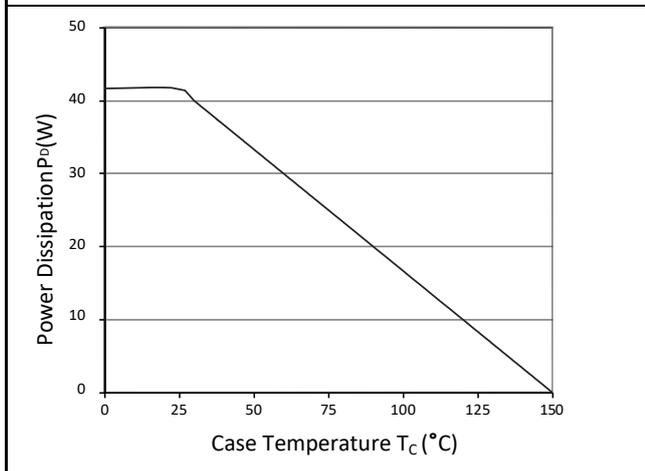


Figure 9. Power Dissipation

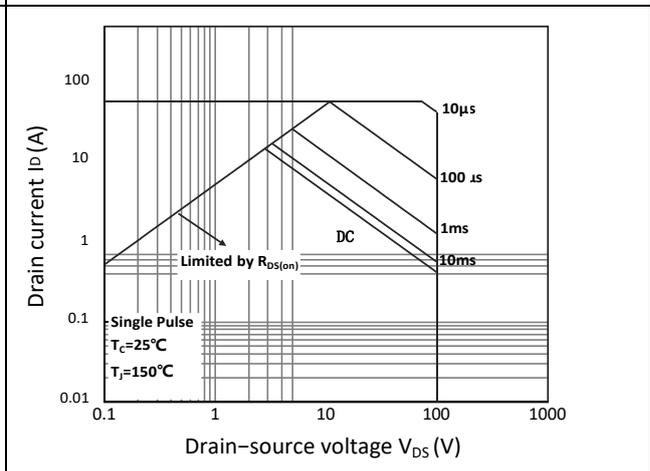


Figure 10. Safe Operating Area

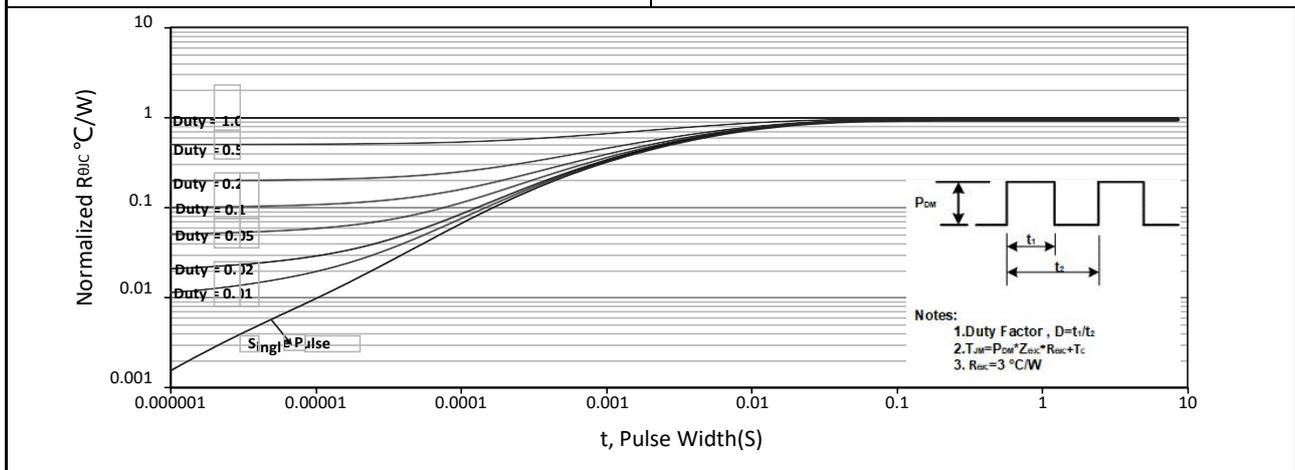
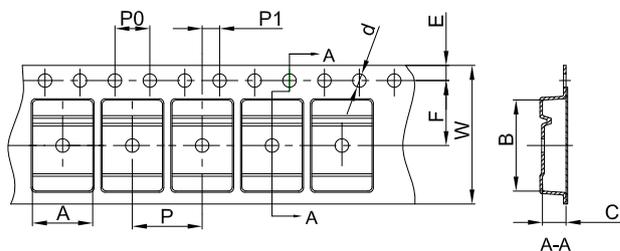


Figure 11. Normalized Maximum Transient Thermal Impedance

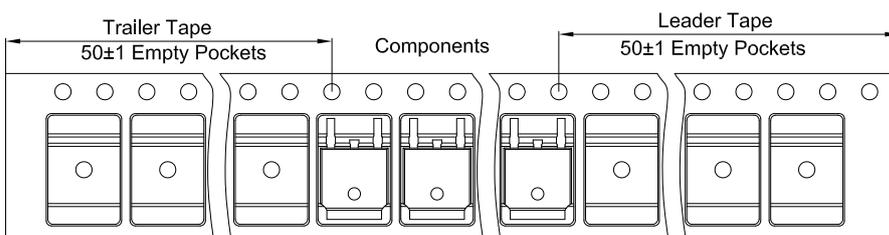
TO-252-2L Tape and Reel

TO-252 Embossed Carrier Tape

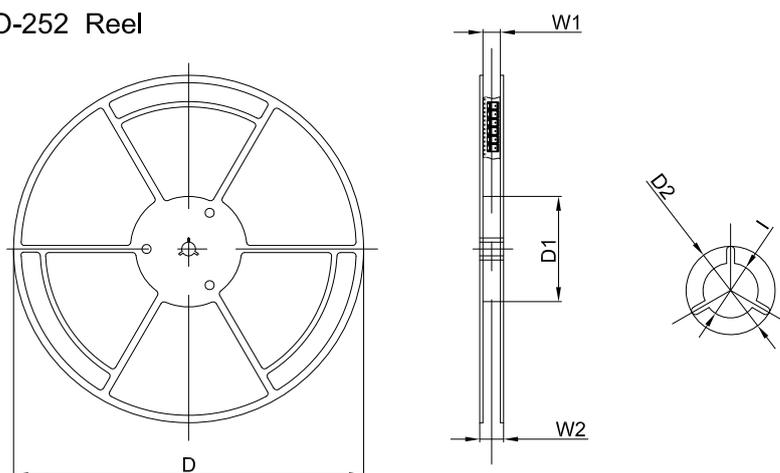


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
TO-252	6.90	10.50	2.70	Ø1.55	1.75	7.50	4.00	8.00	2.00	16.00

TO-252 Tape Leader and Trailer

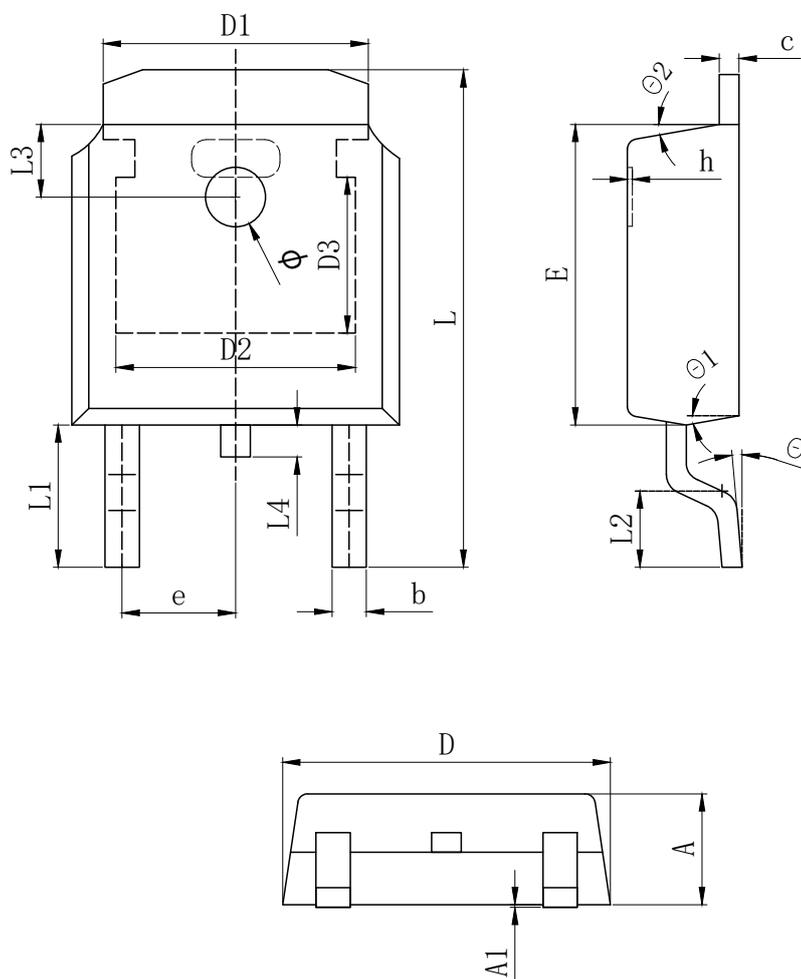


TO-252 Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	W1	W2	I
13"Dia	330.00	100.00	Ø21.00	16.40	21.00	Ø13.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13inch	2,500 pcs	340×336×29	25,000 pcs	353×346×365	



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c (电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
Φ	1.100	1.200	1.300
θ	0°		8°
θ 1	9° TYP		
θ 2	9° TYP		

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